deposition source including, for example, a sputtering source. In another embodiment, the source **311** is a chemical vapor deposition source including, for example, a direct ion source using a hydrocarbon precursor gas. Beam **312** is focused on a location **319** on the substrate **309** whereat the material of the beam **312** is deposited to form a film of an energy-storage device. An assist source **313** is provided in the chamber **307** and produces a beam of energized particles **314** directed at least adjacent to the location **319** on the substrate **309**. In some embodiments, the assist source is an energized ion-producing source. In some embodiment, the assist source **313** is offset from the first source **311** such that the beams from these sources are not coincident. The energized particle beam **314** provides the energy that is required to control the growth and stoichiometry of the material in the first beam **312** into a crystalline structure on the substrate **309** as is explained in greater detail herein. In one embodiment, the energized particle beam **314** also provides elements that are required in the film being deposited. In another embodiment, beam **314** is directed at least near location **319** such that sufficient energy to form the desired crystal structure and stoichiometry of the film being deposited is supplied by beam **314** to the material in first beam **312**. In some embodiments, the deposition system **305** includes at least one additional assist source **313**A. In some embodiments, each of the sources **313**A provides an additional assist beam **314**A that provides energy to arriving adatoms at the substrate. Various embodiments of assist beams **314** are described below.

[0156] **FIG. 3B** shows another embodiment of a deposition apparatus **305**. The assist source **313** produces an energy beam **314** that travels along a path that is essentially normal to the substrate **319**. The source of material to be deposited **311** is offset from assist source **313**. In some embodiments, source **311** produces a beam of adatoms **312** that travels along a path that is non-normal to the substrate **319**. The energy beam supplies energy to the adatoms from beam **312** as described herein.

[0157] **FIG. 4** is a view substantially similar to **FIG. 3**A, except that depositing apparatus **405** includes an assist source **413** for producing the energized beam that is pivotally mounted to a bracket fixed in the chamber **307**. The assist source **413** pivots to direct the energized particle beam **414** at a desired impingement angle to the surface of the substrate **309**. In an embodiment, the impingement angle is in the range of about 15 degrees to about 70 degrees from normal to the substrate. Accordingly, in some embodiments, the impingement angle is variable. In one embodiment, the impingement angle is about 45 degrees. In some embodiments, the deposition system **405** includes at least one additional assist source **413**A. In some embodiments, each of the sources **413**A provides an additional assist beam **414**A that provides energy to arriving adatoms at the substrate. In some embodiments, the energy provided by assist beam **414** differs from the energy provided by at least one of assist beams **414**A. In some embodiments, the assist beam **414** and **414**A need not simultaneously transmit energy to the adatoms. In some embodiments, the means by which the beams **414** and **414**A transmit energy are different. In some embodiments, the material in beams **414** and **414**A are different.

[0158] **FIG. 5A** is a view substantially similar to **FIG. 3** except that depositing apparatus **505** includes a plurality of first deposition sources **511**. In one embodiment, each one of the first deposition sources **511** directs its respective beam **512** to the location **319** on the substrate **309**. In some embodiments, every one of the first sources **511** produces a beam **512** including the same material. In other embodiments, at least of the first sources **511** produces a beam **512** of a material that is different than that of another of the first sources **511**. In some embodiments, the materials from the plurality of first beams **512** combine at the location **319** to form the desired film. In other embodiments, the materials in first beams **512** combine with material from assist beam **314** to form the desired film. In one embodiment, one of the first sources **511** directs its beam **512** to the substrate **319** but away from the location **319**. In some embodiments, a plurality of assist sources **313** provide energy to the adatoms of beams **512**.

[0159] **FIG. 5B** shows another embodiment of a depositing apparatus **505**B. A plurality of assist sources **313** is positioned to provide energy to a forming film at the substrate **319**. A plurality of material sources **511**A, **511**B, and **511**C supply material to the chamber **307** and adjacent the surface of the substrate **319**. In some embodiments, each of the material sources **511**A, **511**B, and **511**C provide a same material and, thus, have the ability to provide a greater quantity than one of the sources alone. In some embodiments, at least one of the material sources **511**A, **511**B, and **511**C provides a material different than another of the material sources. In some embodiments, these different materials react at the in chamber **307** to create the adatom material that will form a film on the substrate **319**. In some embodiments, at least one of the material sources **511**A, **511**B, and **511**C provides a precursor material into chamber **307** and another of the material sources provides a reactant material into the chamber. The precursor and reactant material react together to create the material that will form the film. In some embodiments, at least one of the material sources **511**A, **511**B, and **511**C includes a chemical reactor in which chemicals react. This source then injects the resultant material into the chamber. The resultant material is included in the film fabrication process.

[0160] **FIG. 6** is a view substantially similar to **FIG. 5A** except that depositing apparatus **605** includes a plurality of first deposition sources **511** and a pivotable assist source **413**. In some embodiments, this provides more material to a given deposition location. In some embodiments, this provides deposition at multiple locations. In still other embodiments, this allows different materials from different sources to be combined.

[0161] **FIG. 7** shows another embodiment of a depositing apparatus **705** according to the teachings of the present invention. Depositing apparatus **705** includes a reaction chamber **707** in which is positioned an elongate, flexible substrate **709** on which an energy-storage device is to be fabricated. The substrate **709** is fed from a source roll **710** over an arched thermal control surface **715** and taken up by an end roll **713**. A first material source **711** is provided in the chamber **707** and is a physical deposition source. First source **711** produces a beam of adatoms **712** of a material to be deposited on the substrate **709**. In one embodiment, the first source **711** is an arc source including, for example, a cathodic arc source, an anodic arc source, and a CAVAD arc source. In another embodiment, the first source **711** is a physical vapor deposition source including, for example, a